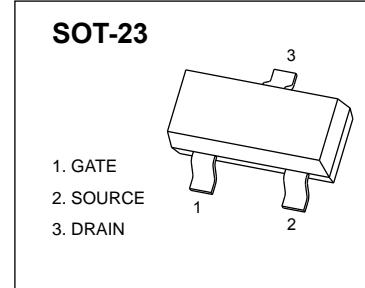


# SOT-23 Plastic-Encapsulate MOSFETS

P-Channel 20-V(D-S) MOSFET

$V_{(BR)DSS}$	$R_{DS(on)Typ}$	$I_D$
-20 V	38mΩ@-4.5V	-4A
	50mΩ@-2.5V	
	70mΩ@-1.8V	



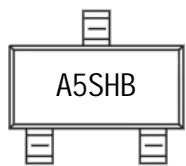
## FEATURE

- TrenchFET Power MOSFET

## APPLICATION

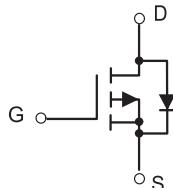
- PA Switch
- Load Switch

## MARKING



A5SHB= Device code

## Equivalent Circuit



## Maximum ratings ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 10$	
Continuous Drain Current	$I_D$	-4	A
Pulsed Drain Current	$I_{DM}$	-15	
Continuous Source-Drain Diode Current	$I_S$	-0.59	
Maximum Power Dissipation	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	°C/W
Operation Junction and Storage Temperature Range	$T_J, T_{stg}$	-50 ~ +150	°C

## MOSFET ELECTRICAL CHARACTERISTICS

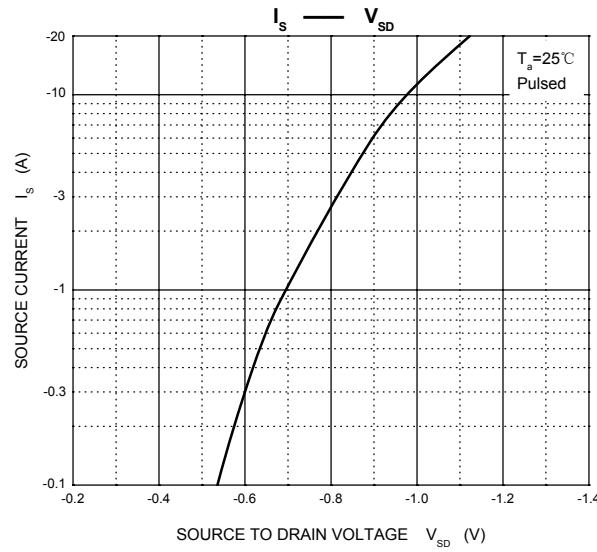
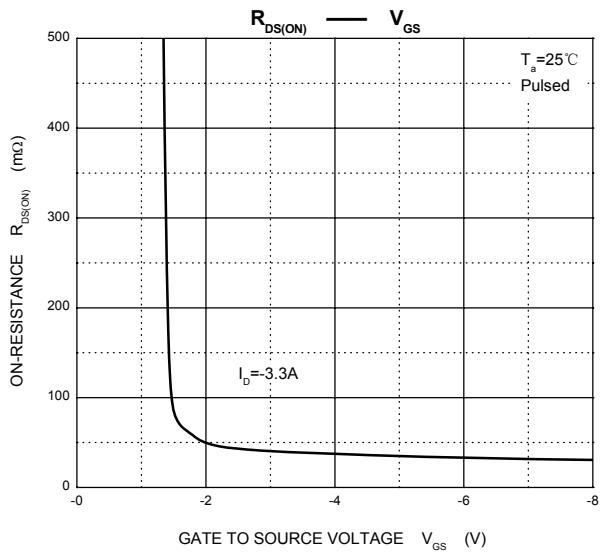
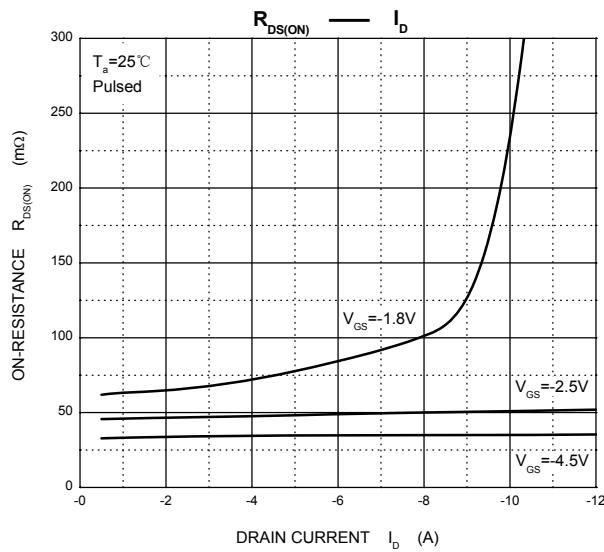
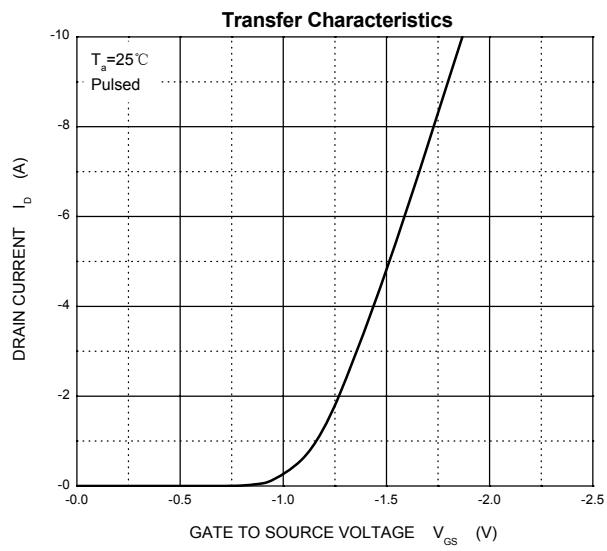
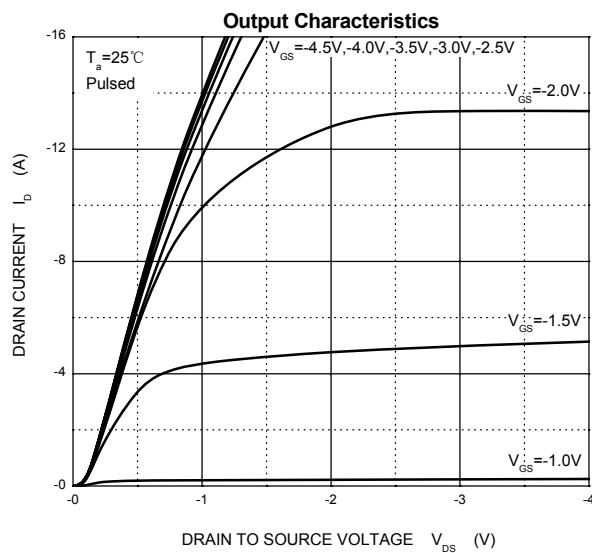
**T<sub>a</sub>=25 °C unless otherwise specified**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -10µA	-20			V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±12V			±100	nA
Zero Gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V			-1.0	µA
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA	-0.4		-1.0	V
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.4A		0.038	0.060	Ω
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.0A		0.050	0.075	
		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -2.5A		0.070	0.095	
Forward tranconductance	g <sub>fS</sub>	V <sub>DS</sub> = -5V, I <sub>D</sub> = -3.4A	3			S
Forward diode voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.6A			-1.2	V
<b>Dynamic</b>						
Input capacitance <sup>a,b</sup>	C <sub>iss</sub>	V <sub>DS</sub> = -6V, V <sub>GS</sub> = 0V, f = 1MHz		715		pF
Output capacitance <sup>a,b</sup>	C <sub>oss</sub>			170		
Reverse transfer capacitance <sup>a,b</sup>	C <sub>rss</sub>			120		
Total Gate charge <sup>a</sup>	Q <sub>g</sub>	V <sub>DS</sub> = -6V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.3A			13	nc
Gate-Source charge <sup>a</sup>	Q <sub>gs</sub>				1.2	nc
Gate-Drain charge <sup>a</sup>	Q <sub>gd</sub>				2.2	nc
<b>Switching<sup>a,b</sup></b>						
Turn-on delay Time	t <sub>d(on)</sub>	V <sub>GEN</sub> = -4.5V, V <sub>DD</sub> = -6V, I <sub>D</sub> = -1.0A, R <sub>G</sub> = 6Ω, R <sub>L</sub> = 6Ω			25	ns
Rise time	t <sub>r</sub>				55	
Turn-off delay time	t <sub>d(off)</sub>				90	
Fall time	t <sub>f</sub>				60	

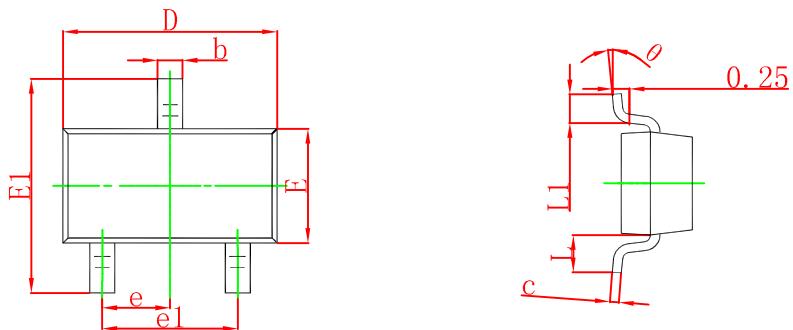
**Notes :**

a. Pulse Test : pulse width ≤300µs, duty cycle ≤2%.

b. These parameters have no way to verify.

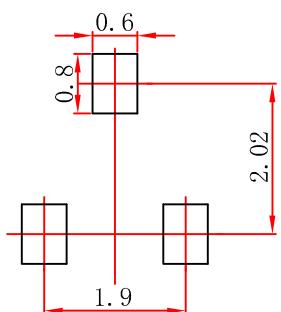


### SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°

### SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.